Carbon Nanotube Them al Transport: Ballistic to Di usive

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We propose to use $l_0 = (l_0 + L)$ for the energy transm ission covering both ballistic and di usive regimes, where l_0 is mean free path and L is system length. This formula is applied to heat conduction in carbon nanotubes (CNTs). Calculations of thermal conduction show: (1) Thermal conductance at room temperature is proportional to the diameter of CNTs for single-walled CNTs (SW CNTs) and to the square of diameter for multi-walled CNTs (MW CNTs). (2) Interfaces play an important role in thermal conduction in CNTs due to the symmetry of CNTs vibrational modes. (3) When the phonon mean free path is comparable with the length L of CNTs in ballistic-di usive regime, thermal conductivity goes as L. The elective exponent is numerically found to decrease with increasing temperature and is insensitive to the diameter of SW CNTs for Umklapp scattering process. For short SW CNTs (0:1 m) we nd 0:8 at room temperature. These results are consistent with recent experimental notings.

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Carbon nanotubes (CNTs) have been reported to have rem arkable electrical, mechanical, and therm alproperties, making them the idealm aterial for various engineering applications. 1,2 Of particular interest in this letter is therm al conduction of CNTs. For example, the anom alous enhancem ent of them al conductivity has been experim entally observed in CNTs composites3. However, many con icting results of CNTs thermal conduction have been reported both theoretically and experim entally. The values of CNTs them al conductivity ranging from 30W =mK to 6600W =mK have been reported at room temperature. 4,5,6,7,8,9 These drastically dierent values make it necessary to clarify which is reliable and what are the conditions for obtaining such values. Therm al conduction in CNTs may dier from the predictions of Fourier's law based on bulk materials because the phonon mean free path (MFP) can be comparable to the length of CNTs. Ballistic phonon thermal transport behavior in CNTs has been observed in molecular dynamic (MD) simulations^{7,9} and recently in experim ents. 10,11 However, so far as we know, no satisfactory theory has been able to cover both ballistic and di usive region. Landauer form ula 12 takes care of ballistic therm al transport, while Boltzm ann equations 13,14 cannot go over to purely ballistic transport.

In this letter, we propose a form ula for therm alconduction covering the range from ballistic to di usive transport. With this formula, we discuss the CNTs therm al conduction's dependence on the tube diameter and tube length, as well as interface e ect.

For therm all transport in quasi-one-dimensional system, the therm alconductivity can be written as 15

$$= \frac{L}{S} \sum_{\substack{n, v_n > 0}}^{X} \frac{dq}{2} \sim !_n (q) v_n (q) \frac{ef}{eT} T_n (q; !_n); \qquad (1)$$

where L and S are the length and cross-section area of the system, T_n $(q;!_n)$ the energy transm ission for the n-th branch wave at longitudinal momentum q, angular frequency $!_n$, and $f(!_n;T)$ is the Bose-E instein distri-

bution at tem perature T. vn is group velocity along the direction of thermal transport given by $v_n = 0!_n = 0q$. The integration over momentum q is within the rst Brillouin zone. The central problem is to calculate the energy transm ission T_n (q;! $_n$). W e propose that energy transmission can be calculated for three dierent thermaltransport regimes according to the relation between the MFP l_0 (q) and the length of the system L. (1) Ballistic regime lo L. The MFP is much larger than the length of the system. Thermal transport in this regime can be described by Landauer quantum transport formula. 15 There are two equivalent methods for calculating energy transm ission resulting from boundary, conjunction, or defect scattering from atom istic point of view: the scattering boundary mode match method 15 and the non-equilibrium G reen function method. (2) L. The MFP is Ballistic-di usive regime where lo com parable with the length of the system. In this regime, the energy transm ission is approximated by $T_n(q;!_n) =$ $l_0 = (L + l_0)$, as has been shown in Ref. 17 for electronic transport. (3) Diusive regime 10 L. The M FP is much smaller than the length of the system. In this regim e, T_n (q;! n) ' l_0 =L . So therm all conductivity in this lim it is given by the well-known Boltzmann-Peierls form ula $= \frac{1}{S} \sum_{n=0}^{dq} 2^n \cdot !_n \ (q) v_n \frac{\theta \cdot f}{\theta \cdot T} \cdot l_0^n \ (q) \ .$

D iam eter dependence. Here we assume that the thermal transport in CNTs is in the ballistic regime. To simplify the discussion and catch the essential character of ballistic thermal transport in CNTs, we assume the energy transmission $T_n\left(q;!_n\right)$ t 1. This assumption is justified for short CNTs with few imperfections at moderate temperatures 9,10 . Several different denitions for the cross section for CNTs have been used in Ref. 4,5,6,7,8,9, because it is not well dened. To circum vent this ambiguity, we would like to use more experimentally oriented physical quantities: thermal conductance $G_{th} = S = L$ to measure the property of thermal conduction of CNTs. In our computation, phonon dispersion for single-walled CNTs (SW CNTs) is calculated

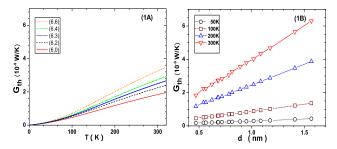


FIG. 1: ThermalConductance for SW CNTs. (1A) Dierent chirality SW CNTs as a function of temperature. (1B) Dierent diameter SW CNTs at $T=50;100;200;300 \,\mathrm{K}$ respectively.

using the method and force constants in Ref. 1. The group velocity is calculated from the phonon dispersion by the method in Ref. 15. The results of therm alconduction for di erent chirality and diam eter SW CNTs at di erent tem peratures are illustrated in Fig. 1. It can seen from Fig. 1 that at low temperature, for example $T = 50 \,\mathrm{K}$, therm al conductance alm ost does not change with diameter or chirality. At the extremely low temperature limit, all CNTs give the quantized universal therm al conductance 11 4 $^{2}k_{B}^{2}$ T=3h, which corresponds to the four channels of quantum transport for acoustic phonons. When temperature increases, more optical phonon channels will contribute to them al transport. However, it is contrary to the intuitive conclusion that therm al conductance at high tem perature T will be proportional to the total numbers N $_{\rm ph}$ of phonon channels in CNTs. Therm alconductance at high temperature is proportional to the diam eter d of CNTs, irrespective of their chirality. For example, the ratio of channel number SW CNTs (6;4) to (6;0) is N $_{\rm ph}^{\rm (6;4)}$ =N $_{\rm ph}^{\rm (6;0)}$ 6:33, while their diam eter ratio is $d^{(6;4)}=d^{(6;0)}$ 1:45. It can be seen from Fig. 1 that the ratio of therm alconductance at 300 K is about 1:45, not 6:33. This proportionality to diam eter is in plicitly dem onstrated in Ref. 14 by counting the number of phonon branches at frequency! to calculating the transmission. This simple result can be easily understood if we approximate the integrand in Eq. (1) by a constant, obtaining the result that Gth is proportional to the total number of modes divided by the unit cell length, which is proportional to d. For M W CNTs, if them al conductance above certain temperature can be added from the contribution of each shell independently, the total therm alconductance will be $_$ rdr $_$ d². The dissipation power results in Ref. 10 have a tendency of d^2 . It should be noted that the above results only characterize the therm al conductance in pure ballistic regime. In actual experim ents, the situation is more complicated for them al conductance in sub-microm eter lengths. For exam ple, the contact interface and phonon scattering are inevitable in experim ent. We will discuss these elects on therm al conduction in CNTs.

Interface e ect. Interface e ect on CNIs thermal transport has been studied through e ective medium

theory 18 and empirical random walk simulation. 19 However they are only rough models, not from rst principles. Here we consider the interface e ect from a lattice point of view. We consider an extreme case, where the sem iconductor nanotube junction structure (11,0) and (8,0) is rst constructed by a geom etrical m ethod as in Ref. 1. The structure is optim ized by a second-generation B renner potential²⁰ to let the atom s get their equilibrium positions. The force constants are derived numerically from the same potential. The phonon dispersion is calculated from these linearized force constants. Four acoustic branches are considered for energy transport: the longitudinal m ode (LA), doubly degenerate transverse m ode (TA), and the unique twist mode (TW) in nanotubes. Following the scattering boundary method, 15 we calculated the energy transmission across the CNTs conjunction. The details of calculation are presented in Ref. 15. The rejected and the transmitted waves across the junction for the incident LA mode waves are both only LA m odes. We think that this is due to the high sym metrical properties of atom ic motion for nanotubes. The LA and TA m odes are com m on sym m etricalm otions for both the left and right lead. So they propagate through the conjunction. In contrast, the transmissions of the TW mode and many other optical modes are nearly zero or very small. From these results, we consider the interface between CNTs and substrate will in uence the experim entalm easured CNTs therm alconductivity greatly, which has been indicated in experim ental results^{8,10}. We argue that chem ical functional reorganization of the CNT sends or proper choice of the more symmetry-shared substrate m atrix will improve therm altransport of CNTs.

Length e ect. Purely ballistic them al transport will make them al conductivity—diverge linearly with the length L of CNTs. A nom alous them al transport for 1D nonlinear lattice predicts that—will diverge with L as—L. For 1D nonlinear lattice with transversem otion, which is similar to CNTs, it is found = 1=3 through MD simulation and mode-coupling theory. A few results of tube length e ect on them al transport in CNTs have been reported recently through MD simulation 7,9 . A length dependence of the them al transport in CNTs is also observed in experiments 10 . It can be seen from Eq.(1) that them al conductivity will depend on the length of CNTs in ballistic-di usive regime.

The problem to calculate therm al conductivity from Eq. (1) in ballistic-di usive regim e is to compute MFP, which depends on frequency and wave length of the vibration modes, as well as temperature. Assuming that the scattering mechanisms are not coupled, MFP can be written as $1=1_0=1_1$, where the index i denotes various interaction phonon processes. In CNTs, the phonon scattering process may be dierent from that of bulk and is not well known. Here, for simplicity, we rest consider the Um klapp scattering. Um klapp phonon scattering 1_0^{-1} in CNTs has been shown linear T dependence at high temperatures through experiment and is usually given a 1^2 dependency on the frequency.

we take the form $l_U = A = (!^2T)$ for $Um \, k \, lapp \, scattering$ in CNTs, where A is taken to be the same as derived for graphene in Ref. 24. The phonon dispersion is calculated as in Ref. 1. The cross-section area S is de ned as $S = d^2/4$. Results are illustrated in Fig. 2 through Eq. (1) for ballistic-di usive regime in CNTs. We should note that the exponent in Fig. 2 (C,D) is an e ective exponent in a limited length region, not the asymptotic one. 21,22 It can be seen from Fig. 2A that therm alconductivity shows di erent length dependence scaling L for short CNTs (< 0:1 m) and long CNTs (> 10 m), denoted as s and L respectively, when Umklapp scattering in CNTs is considered in ballistic-di usive regime. This is due to the relation between Mg FP and the length of CNTs. A verage MFP l_0 (T) = l₀ (!;T)D (!)d! is calculated from the phonon dispersion relation for CNT (6,6), where D (!) is normalized density of states, satisfying D (!)d! = 1. Figure 2B indicates that average MFP decreases rapidly from 0.25 m to 0.06 m, when tem perature goes up from 50 K to 200 K.W e also calculated average MFP for other chirality CNTs and found little di erence from that of CNT (6,6). Fig. 2C shows the change of $_{\rm S}$ and $_{\rm L}$ with temperature. For exam ple, when $T = 50 \,\mathrm{K}$, the average MFP is as large as $0.25\,$ m and so the $_{\rm S}$ is almost equal to 1. When temperature increases, the MFP becomes shorter, so s and $_{\mbox{\scriptsize L}}$ both decrease with temperature. The dependence of $_{\mathrm{S}}$ and $_{\mathrm{L}}$ on CNTs diam eter is illustrated in Fig. 2D . s almost does not change with the chirality of CNTs 0.83 at room temperature, while $_{\rm L}$ deand gives s

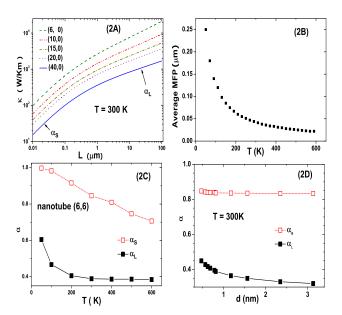


FIG. 2: Length divergence in ballistic-diusive regimes: (2A) Thermal conductivity for dierent chiralities SW C-NTs at $300\,\mathrm{K}$; (2B) A verage m ean free path length for nanotube (6,6) at dierent temperatures; (2C) Change of power law exponent for short and long CNTs with temperature; (2D) Change of power law exponent for short and long CNTs with diam eter;

creases slow by with increase of the diam eter of CNTs, and gives its value about $_{\rm L}$ 0.35 for CNTs with diam eter larger than 1nm at room temperature. This kind of temperature dependence and chirality dependence agrees with MD simulation results. This worth noting that, for CNTs with length less than 0.1 m, = 0.32 and = 0.40 for CNT (5,5) at room temperature are reported by non-equilibrium MD simulation, while 1 is observed using equilibrium MD simulation. For MWCNT with length less than 0.5 m, roughly 1 is reported. We think that the difference for non-equilibrium MD and equilibrium MD comes from the boundary condition because in short CNTs the result should be sensitive to the boundaries.

Next we discuss other phonon scattering mechanisms. If the frequency dependence of MFP is assumed as $1=l_0$! r, then at high temperature the length dependence of therm algonductivity given by Eq. (1) can be estimated $\frac{1}{1=l_0+1=L}d!$ _ L $\frac{r-1}{r}$, that is = (r For Um klapp scattering process, r = 2 and = 0.5which corresponds to the e ective exponent at length about 1 m. For defect scattering mechanism, we have $1=l_0$ _ ! 4, = 0:75. Thus, it can be argued that strong frequency dependence scattering (large r) will not have much help in elim inating them al conductivity divergence, while weak frequency dependence scattering will contribute to elim inating this divergence. Finally, in the very long tube lim it, approaches a constant within our theory.

Conclusions. Crossover in thermal conduction from ballistic to di usive is illustrated. Therm al conductance at room temperature is found _ d for SW CNTs and _ d² for M W C N T s. Interfaces plays an important role in them al conduction in CNTs due to the high symmetrical property of CNTs vibration modes. Possible ways to improve them alconduction in CNTs are suggested. In ballistic-di usive regime, therm al conductivbehaves as L . The e ective exponent m erically found decreasing with increasing temperature and insensitive to the diameter of SW CNTs for Umklapp scattering process. The possible mechanism for the reduction of divergence for therm al conductivity is also discussed. A lthough the formula is still phenomenological, it does cover ballistic and di usive regimes with a sm ooth crossover and gives a reasonably simple picture in the whole tem perature range. This work is supported in part by a Faculty Research Grant of National University of Singapore.

- R. Saito, G. D resselhaus, and M. S. D resselhaus, Physical Properties of Carbons N anotubes, Imperial College Press, 1998.
- J. Hone, in Carbon Nanotubes: Synthesis, Structure, Properties and Application, M. S. Dresselhaus et al., (Eds.), Topics Appl. Phys. 80, 273 (2001).
- ³ S.U.S.Choi et al., Appl. Phys. Lett. 79, 2252 (2001). M. J. Biercuk et al., Appl. Phys. Lett. 80, 2767 (2002). M. B. Bryning et al., Appl. Phys. Lett. 87, 161909 (2005).
- S. Berber, Y. Kwon, and D. Tomanek, Phys. Rev. Lett. 84,4613 (2000).P.Kim et al., Phys. Rev. Lett. 87,215502 (2001).M. Fujii et al., Phys. Rev. Lett. 95,065502 (2005).
- J.H one et al, Appl.Phys.Lett.77,666 (2000).T.Y.Choi et al, Appl.Phys.Lett.87,013108 (2005).
- W. Yiet al., Phys. Rev. B 59, R 9015 (1999). J. Che, T. Cagin and W. A. Goddard III, Nanotechnology 11, 65 (2000).
- ⁷ S.M aruyam a, Physica B 323, 193 (2002); G. Zhang and B.Li, J. Chem. Phys. 123, 114714 (2005).
- ⁸ E.Pop et al., Phys. Rev. Lett. 95, 155505 (2005).
- ⁹ Z.Yao, J.-S.W ang, B.Li, and G.Liu, Phys. Rev. B 71, 085417 (2005).

- $^{\rm 10}$ H $\mbox{-Y}$. Chiu et al., cond-m at/0507004.
- ¹¹ E.Brown et al., Appl. Phys. Lett. 87, 023107 (2005).
- ¹² L.G.C.Rego and G.K irczenow, Phys.Rev.Lett.81, 232 (1998).
- ¹³ G.Chen, Phys. Rev. Lett. 86, 2297 (2001).
- ¹⁴ N.M ingo and D.A.Broido, Phys. Rev. Lett 95, 096105 (2005); Nano. Lett. 5, 1221 (2005).
- ¹⁵ J. W ang and J.S. W ang, cond-m at/0505401 and cond-m at/0509092.
- ¹⁶ N.M ingo and Y.Liu, Phys.Rev.B 68, 245406 (2003).
- ¹⁷ S. Datta, Electronic Transport in Mesoscopic Systems, Cambridge Univ. Press, 1995, p. 63.
- ¹⁸ C.W .Nan et al., Appl. Phys. Lett. 85, 3549 (2004).
- ¹⁹ H.M.Duong et al., Appl. Phys. Lett. 87, 013101 (2005).
- ²⁰ D.W. Brenner et al., J. Phys.: Condens. M atter. 14, 783 (2002).
- 21 S.Lepri, R.Livi, and A.Politi, Phys.Rep. 377, 1 (2003).
- ²² J.S.W ang and B.Li, Phys.Rev.Lett.92,074302 (2004).
- P.G. K lem ens, in Therm al Conductivity, R.P. Tye, Ed., A cadem ic Press, London, 1, 1 (1969).
- ²⁴ P.G.K lem ens and D.F.Pedraza, Carbon 32,735 (1994).